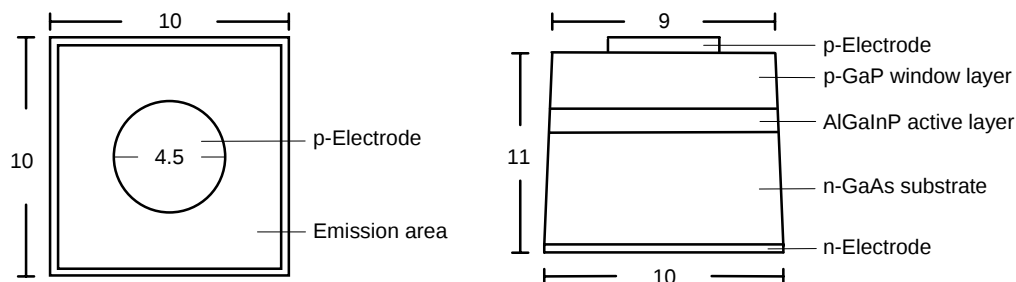


■ **Features :**

- HP MOVPE process wafer
- Superior VF and thermal stability
- Good for high current / brightness applications
- High light output at four sides results high total light output and wide view angle after packaging
- High reliability
- Excellent bondability

■ **Typical Applications :**

- Automotive Signal Lamps: Stop, Tail, Center High Mount Stop Lights
- Automotive Interior Lighting
- Traffic Signal Modules: Barricades
- Industrial Products

■ **Outline Dimensions :** (Unit: mil)■ **Physical Structure :**

Chip dimension	Chip size	10.0 mils x 10.0 mils
	Thickness	11.0 mils
	Emission area	9.0 mils
	Bonding pad	4.5 mils
Electrode	Top: P (anode)	Aluminum
	Backside: N (cathode)	Gold alloy
Surface condition	Not frosted	

■ **Electro-Optical Characteristics :** (Ta = 25°C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	$I_F = 20 \text{ mA}$	-	1.85	2.50	V
Reverse Voltage	V_R	$I_R = 10 \mu\text{A}$	5	-	-	V
Wavelength	λ_D	$I_F = 20 \text{ mA}$	-	615	-	nm
	Hue		606	614	626	
Spectral width at half height	$\Delta\lambda$	$I_F = 20 \text{ mA}$	-	18	-	nm
Luminous Intensity	I_V	$I_F = 20 \text{ mA}$	C1	35	-	mcd
			D1	45	-	
			E1	65	-	
			F1	75	-	

■ Typical Electro-Optical Characteristics Curve:

Fig 1. Forward Current vs. Forward Voltage

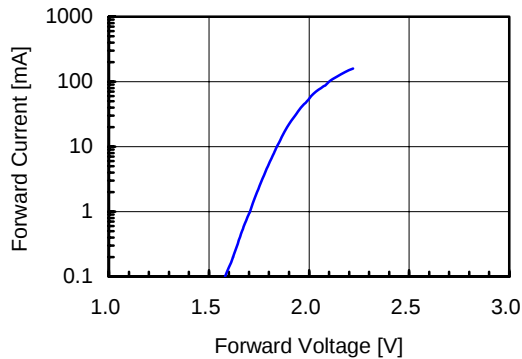


Fig 2. Relative Intensity vs. Forward Current

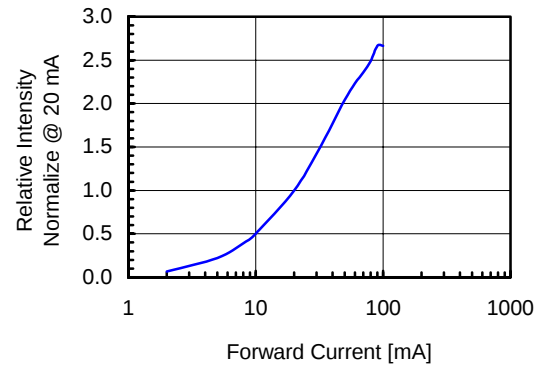


Fig 3. Forward Voltage vs. Temperature

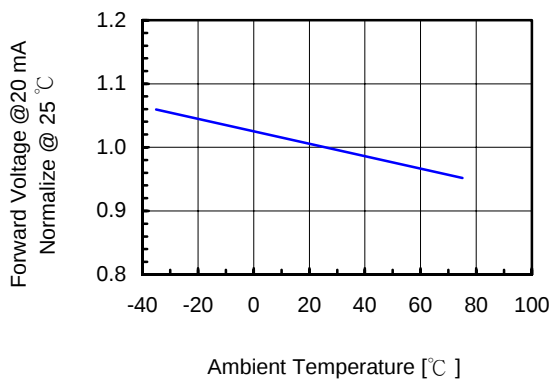


Fig 4. Relative Intensity vs. Temperature

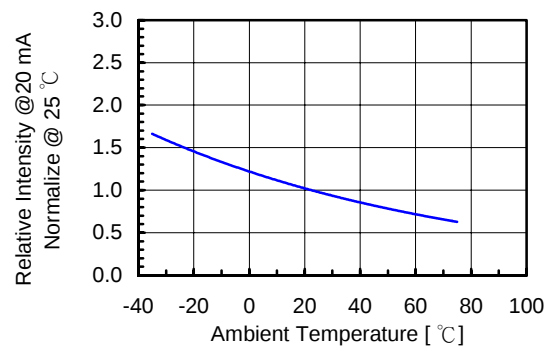
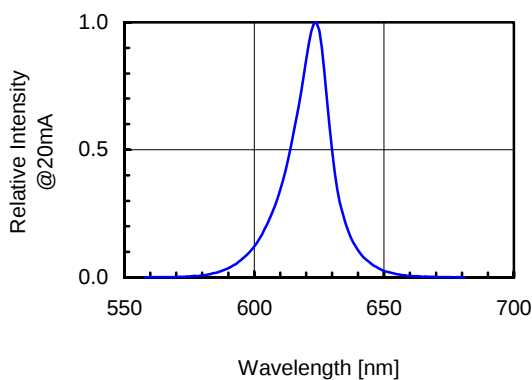


Fig 5. Relative Intensity vs. Wavelength



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